NSN 5962-01-370-0392

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Maximum Power Dissipation Rating:
300.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
An/fps-124
Features Provided:
Programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, bipolar, programmable, logic monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 12.0 volts total supply and -1.5 volts absolute input and 5.5 volts absolute input
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883
standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 printed circuit
Specification Data:

Departure From Cited Designator:

02 type and r case and a finish and 204 number

Specification Or Standard:

67268-85065 government standard and 56232-1219256 manufacturers specification control

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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